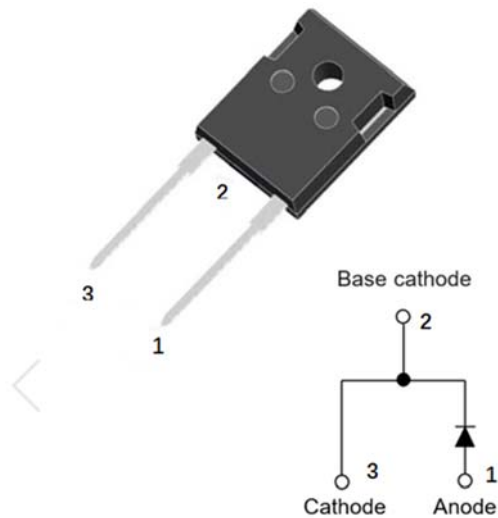


Silicon Carbide Schottky Diode

V_{RRM}	1200V
$I_F (135^\circ\text{C})$	38A
Q_C	153nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

Package: TO-247AC

Terminals: Tin plated leads

Polarity: As marked

Maximum Ratings ($T_c=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Device marking code			D112030NG1
Reverse voltage (repetitive peak) @ $T_j=25^\circ\text{C}$	V_{RRM}	V	1200
Reverse voltage (Surge Peak) @ $T_j=25^\circ\text{C}$	V_{RSM}	V	1200
Reverse voltage (DC) @ $T_j=25^\circ\text{C}$	V_{DC}	V	1200
Continuous forward current @ $T_c=25^\circ\text{C}$	I_F	A	81
Continuous forward current @ $T_c=135^\circ\text{C}$			38
Continuous forward current @ $T_c=149^\circ\text{C}$			30
Non-repetitive peak forward surge current @ $T_c=25^\circ\text{C}$, $t_p=10\text{ms}$, Half Sine Wave	I_{FSM}	A	240
Power Dissipation @ $T_c=25^\circ\text{C}$	P_{TOT}	W	394
Power Dissipation @ $T_c=110^\circ\text{C}$			171
i^2t Value @ $T_c=25^\circ\text{C}$, $t_p=10\text{ms}$	i^2dt	A^2S	288
Operating junction and Storage temperature range	T_j, T_{stg}	$^\circ\text{C}$	-55 to +175

Electrical Characteristics

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Typ.	Max.
Forward voltage drop	V_F	V	$I_F=30A, T_j=25^\circ C$	1.54	1.70
			$I_F=30A, T_j=175^\circ C$	2.31	2.70
Reverse leakage current	I_R	μA	$V_R=1200V, T_j=25^\circ C$	1	60
			$V_R=1200V, T_j=175^\circ C$	40	-
Total capacitive charge	Q_C	nC	$V_R=800V, T_j=25^\circ C, Q_C=\int_0^{V_R} I_C(V)dV$	153	-
Total capacitance	C	μF	$V_R=0V, f=1MHz$	2259	-
			$V_R=400V, f=1MHz$	143	-
			$V_R=800V, f=1MHz$	103	-
Capacitance Stored Energy	E_C	μJ	$V_R=800V$	39.5	-

Thermal Characteristics ($T_a=25^\circ C$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	R_{j-c}	$^\circ C/W$	0.38

Characteristics (Typical)

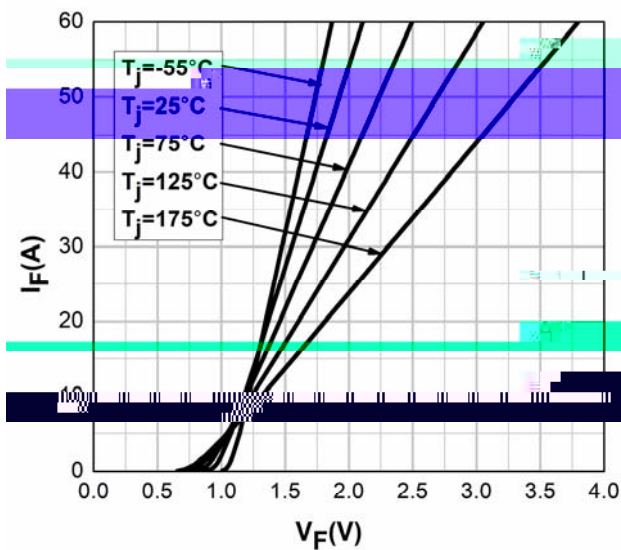


Figure 1. Forward Characteristics

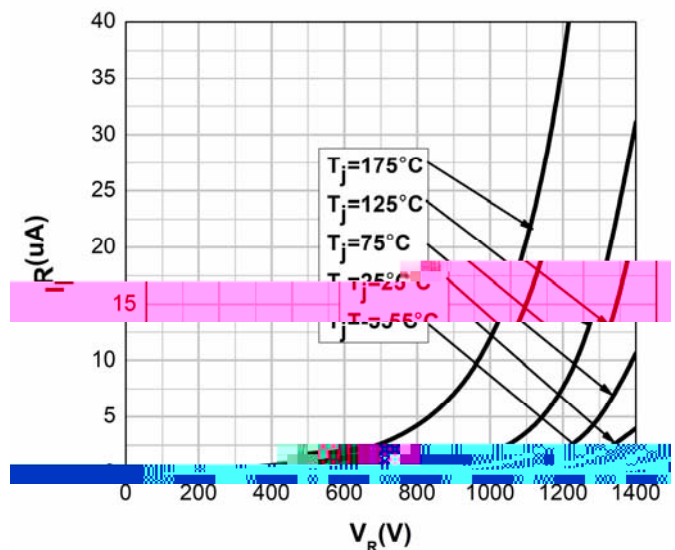


Figure 2. Reverse Characteristic

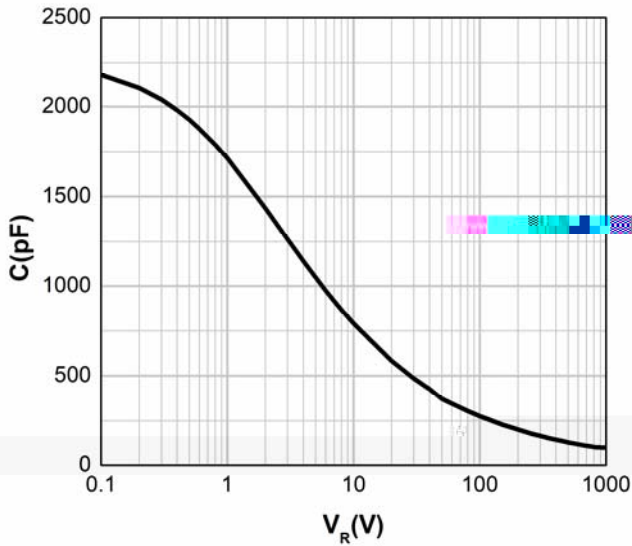


Figure 3. Capacitance vs. Reverse Voltage

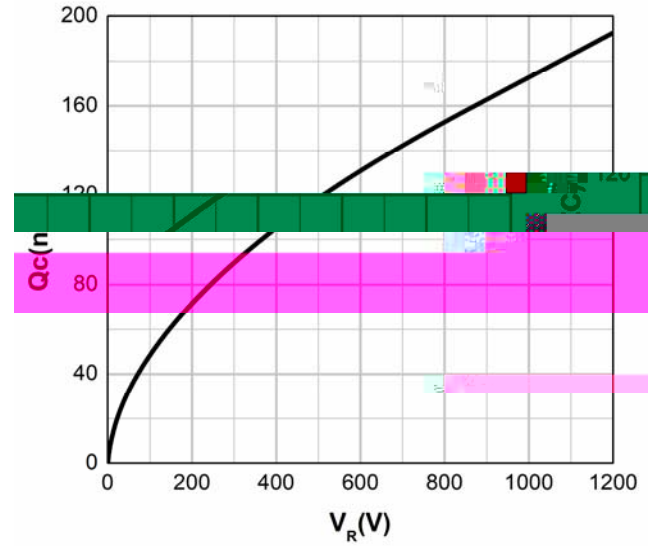


Figure 4. Total Capacitance Charge vs. Reverse Voltage

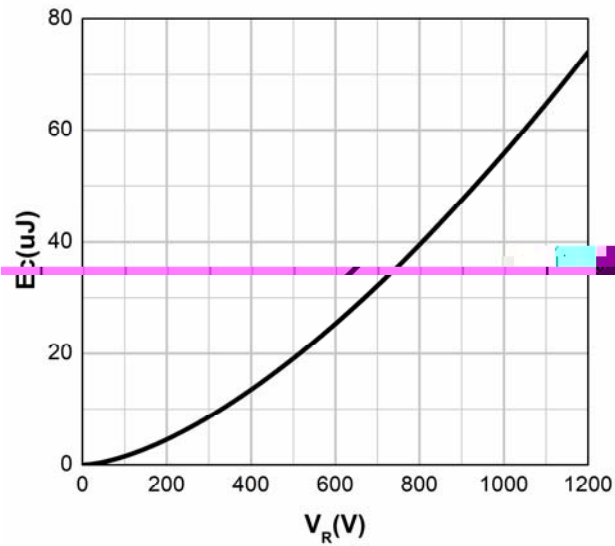


Figure 5. Capacitance Stored Energy

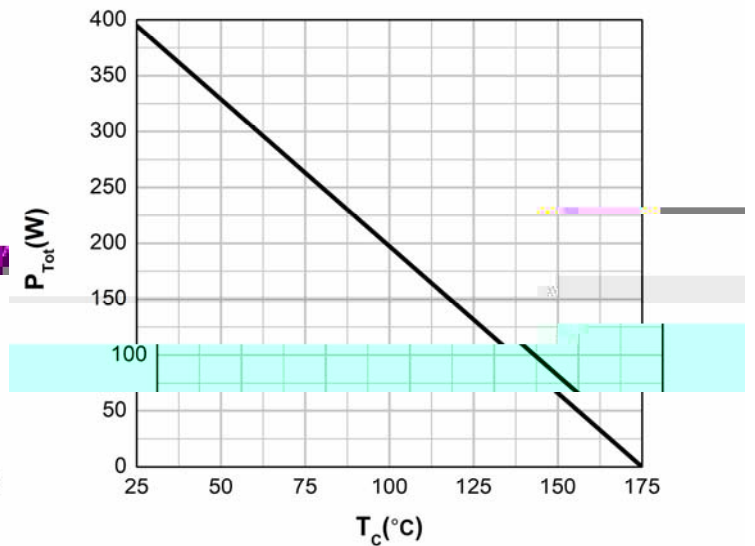


Figure 6. Power Derating

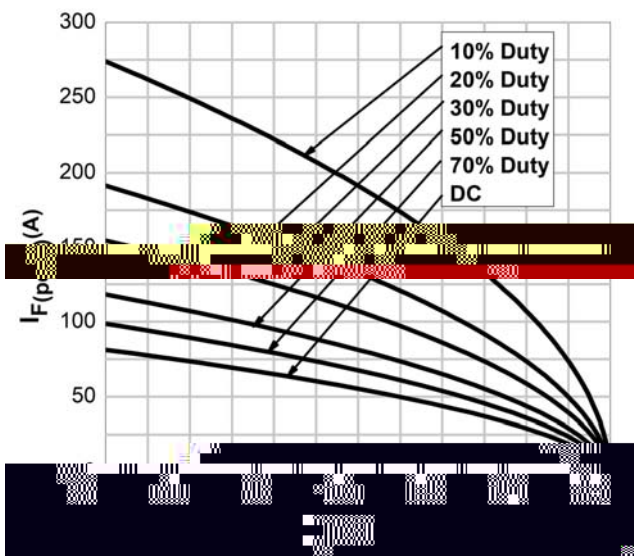


Figure 7. Current Derating

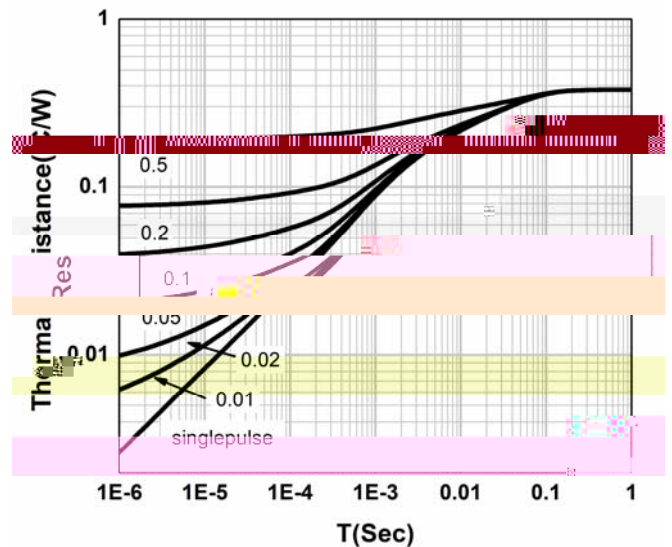


Figure 8. Transient Thermal Impedance

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